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IN THE UNITED STATES PATENT & TRADEMARK OFFICE

IN RE APPLICATION OF :
MICHIHARU MATSUI ET AL : EXAMINER: TRAN, T. F.
SERIAL NO: 09/956,986 :
FILED: SEPTEMBER 21, 2001 : GROUP ART UNIT: 2811
FOR: NONVOLATILE :
SEMICONDUCTOR MEMORY :
DEVICE HAVING ELEMENT :
ISOLATING REGION OF TRENCH :
TYPE AND METHOD OF :
MANUFACTURING THE SAME :

AMENDMENT

ASSISTANT COMMISSIONER FOR PATENTS
WASHINGTON, D.C. 20231

SIR:

In response to the Official Action mailed December 3, 2002, please amend this
application as follows:

IN THE CLAIMS

Please amend Claims 1, 3, 5, 32, 34 and 36 to read as follows:¹

1. A semiconductor device comprising:
- a semiconductor layer;
 - a first insulating film formed on said semiconductor layer;
 - a first electrode layer formed on said first insulating film;
 - an element isolating region comprising an element isolating insulating film formed to extend through said first electrode layer and said first insulating film to reach an inner region

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